



# STW10NC60 STH10NC60FI

N-CHANNEL 600V - 0.6Ω - 10A - TO-247/ISOWATT218  
PowerMesh™II MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STW10NC60	600 V	< 0.75 Ω	10 A
STH10NC60FI	600 V	< 0.75 Ω	10 A (*)

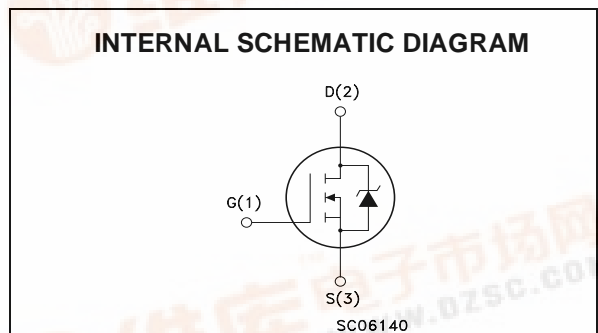
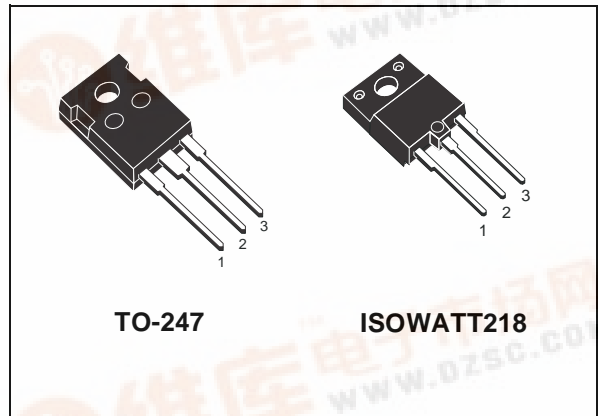
- TYPICAL R<sub>DS(on)</sub> = 0.6 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

### DESCRIPTION

The PowerMESH™II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron\*area figure of merit while keeping the device at the leading edge for what concerns switching speed, gate charge and ruggedness.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVER



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW10NC60	STH10NC60FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	600		V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	600		V
V <sub>GS</sub>	Gate- source Voltage	±30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	10	10 (*)	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	6.3	6.3 (*)	A
I <sub>DM</sub> (1)	Drain Current (pulsed)	40	40 (*)	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	160	60	W
	Derating Factor	1.28	0.48	W/°C
dv/dt	Peak Diode Recovery voltage slope	3.5		V/ns
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	-	2500	V
T <sub>stg</sub>	Storage Temperature	- 55 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature			

(\*) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 10A, di/dt ≤ 100A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

(\*) Limited only by Maximum Temperature Allowed

## STW10NC60 / STH10NC60FI

### THERMAL DATA

		TO-247	ISOWATT218	
Rthj-case	Thermal Resistance Junction-case Max	0.78	2.08	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose	300		°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	10	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	820	mJ

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	600			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±30V			±100	nA

### ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.5 A		0.6	0.75	Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 4.5A		9		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		1420		pF
C <sub>oss</sub>	Output Capacitance			205		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			35		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 300V, I_D = 4.5 A$ $R_G = 4.7\Omega, V_{GS} = 10V$		20		ns
$t_r$	Rise Time	(see test circuit, Figure 3)		16		ns
$Q_g$	Total Gate Charge	$V_{DD} = 480V, I_D = 9.0 A,$ $V_{GS} = 10V$		55	77	nC
$Q_{gs}$	Gate-Source Charge			4.5		nC
$Q_{gd}$	Gate-Drain Charge			31		nC

**SWITCHING OFF**

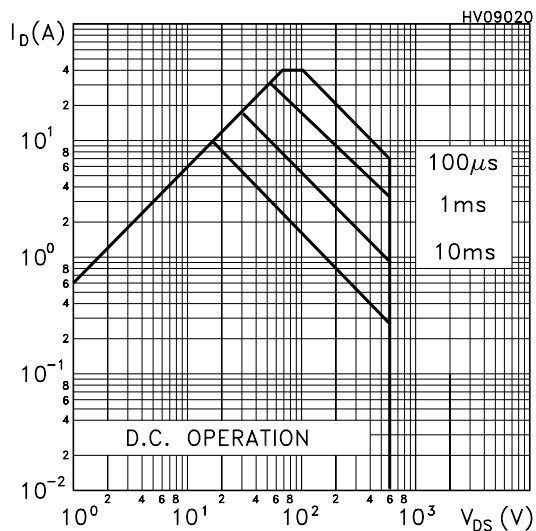
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 300 V, I_D = 4.5 A$ $R_G = 4.7\Omega, V_{GS} = 10 V$		64		ns
$t_f$	Fall Time	(Resistive Load see, Figure 3)		32		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 480V, I_D = 9.0 A,$ $R_G = 4.7\Omega, V_{GS} = 10V$		19		ns
$t_f$	Fall Time	(Inductive Load see, Figure 5)		13		ns
$t_c$	Cross-over Time			32		ns

**SOURCE DRAIN DIODE**

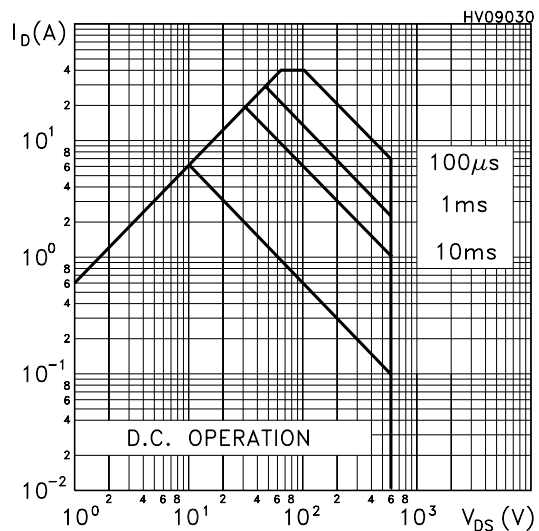
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				10	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				40	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 9 A, V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 9 A, di/dt = 100A/\mu s,$ $V_{DD} = 100V, T_j = 150^\circ C$		600		ns
$Q_{rr}$	Reverse Recovery Charge	(see test circuit, Figure 5)		4.7		$\mu C$
$I_{RRM}$	Reverse Recovery Current			15.5		A

Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

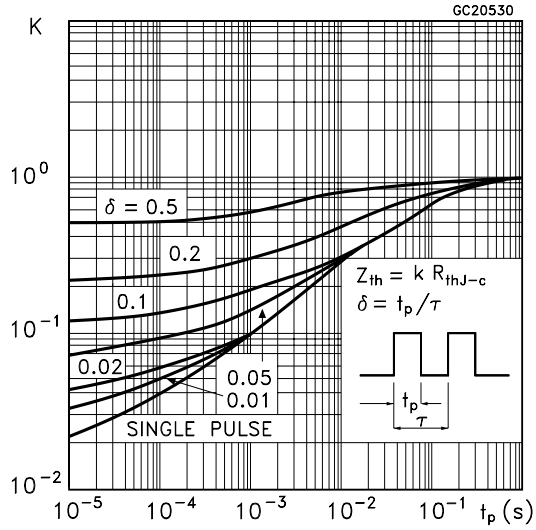
**Safe Operating Area for TO-247**



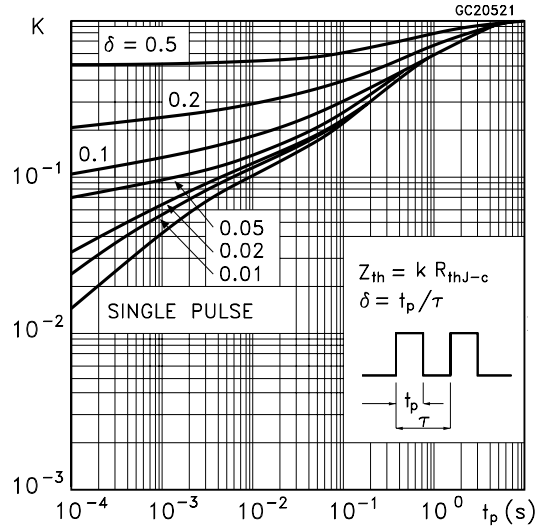
**Safe Operating Area for ISOWATT218**



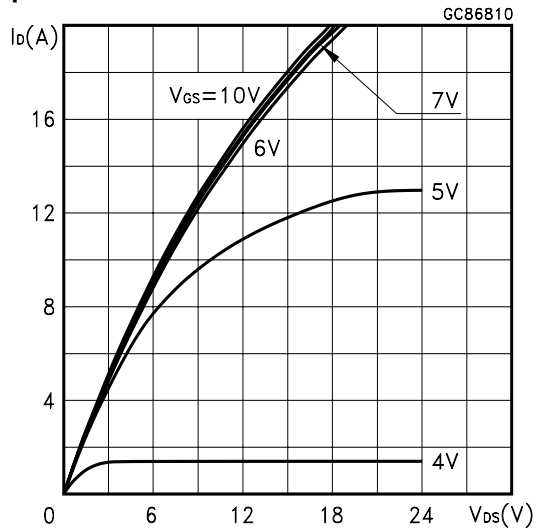
Thermal Impedance for TO-247



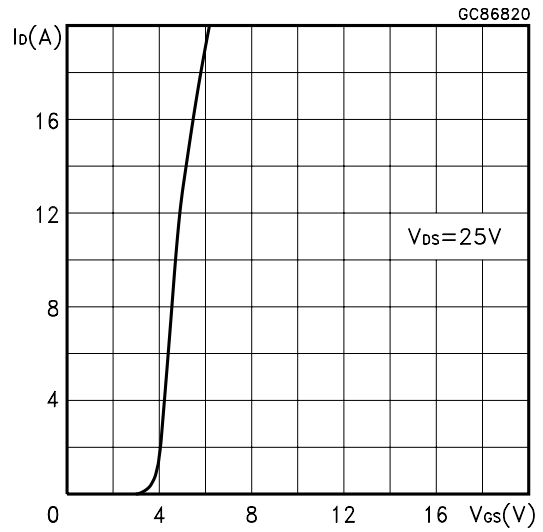
Thermal Impedance for ISOWATT218



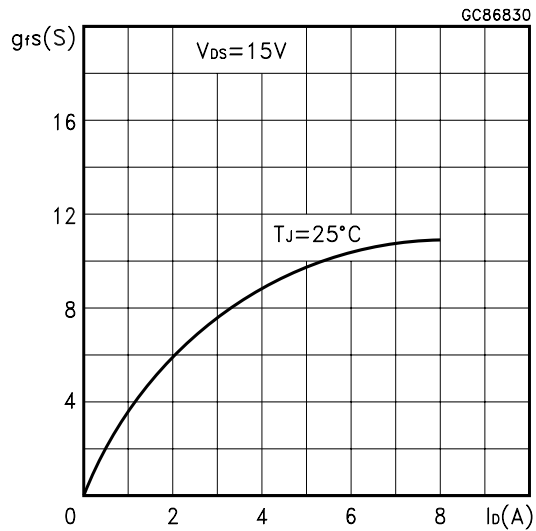
Output Characteristics



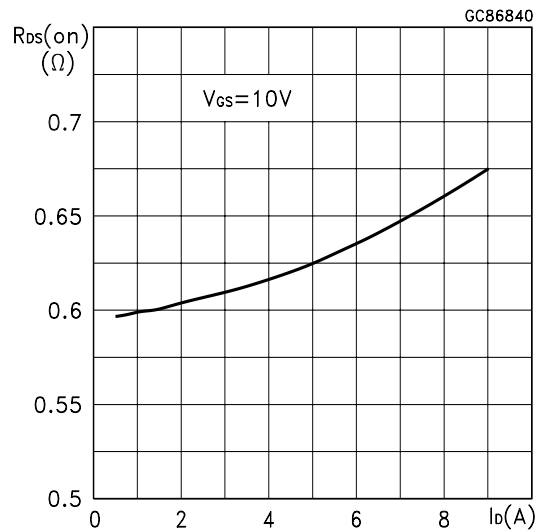
Transfer Characteristics



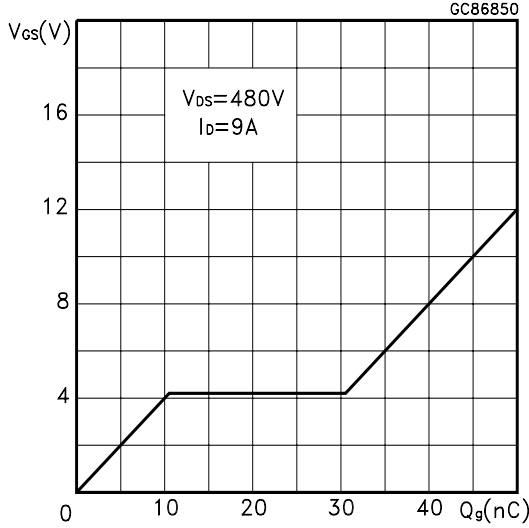
Transconductance



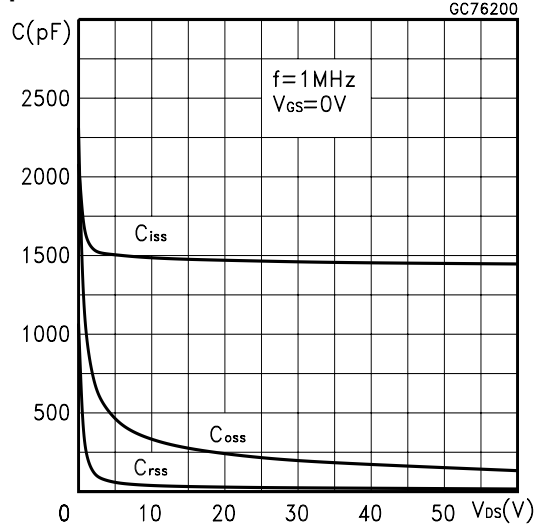
Static Drain-source On Resistance



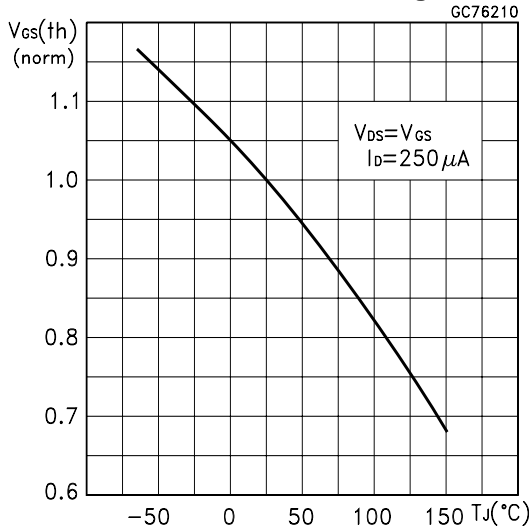
Gate Charge vs Gate-source Voltage



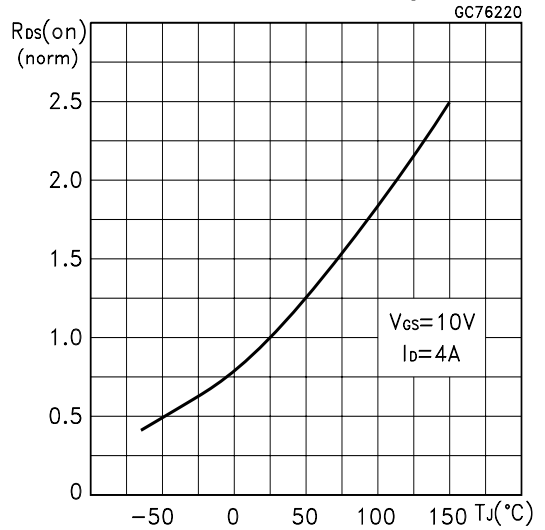
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

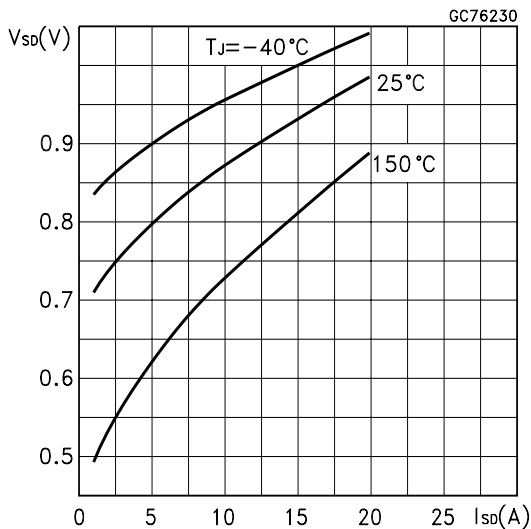


Fig. 1: Unclamped Inductive Load Test Circuit

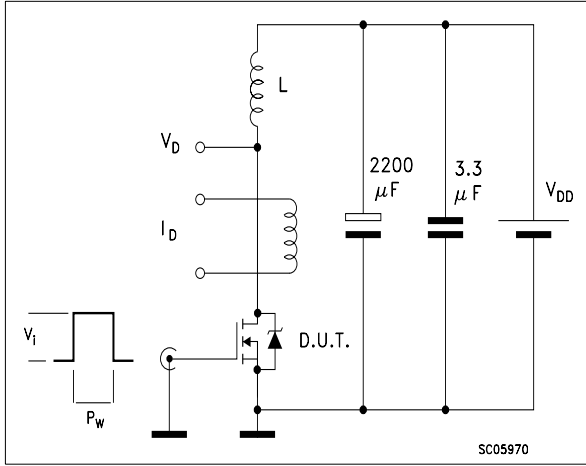


Fig. 2: Unclamped Inductive Waveform

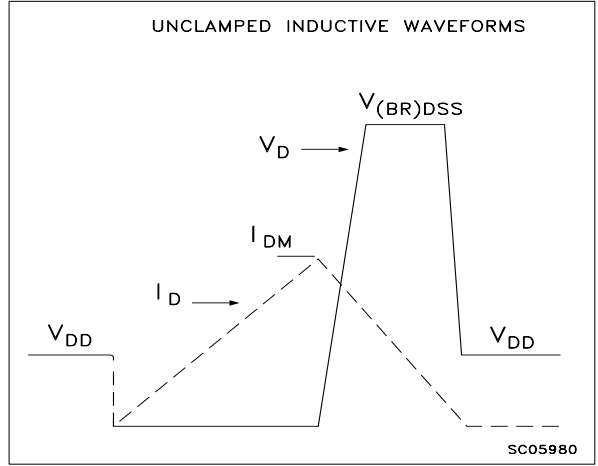


Fig. 3: Switching Times Test Circuit For Resistive Load

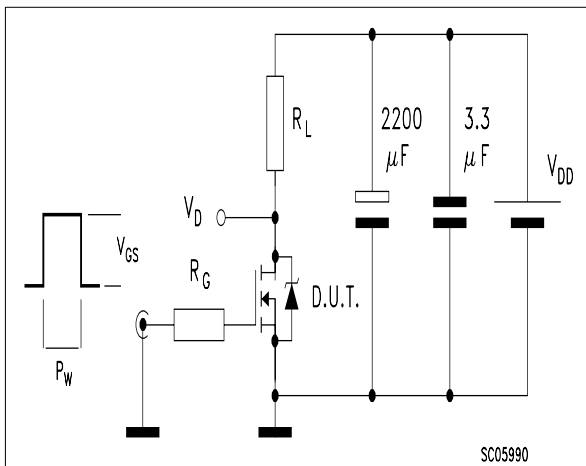


Fig. 4: Gate Charge test Circuit

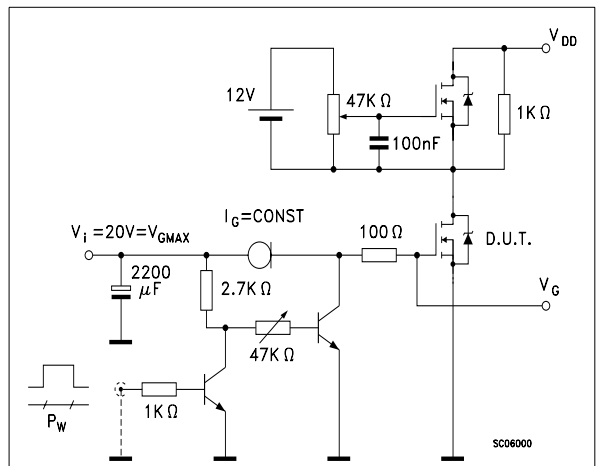
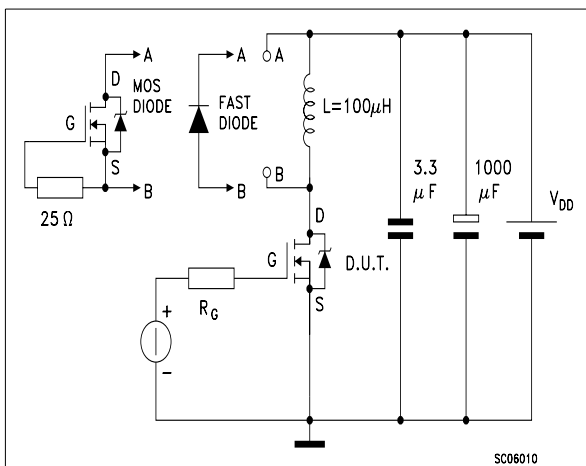
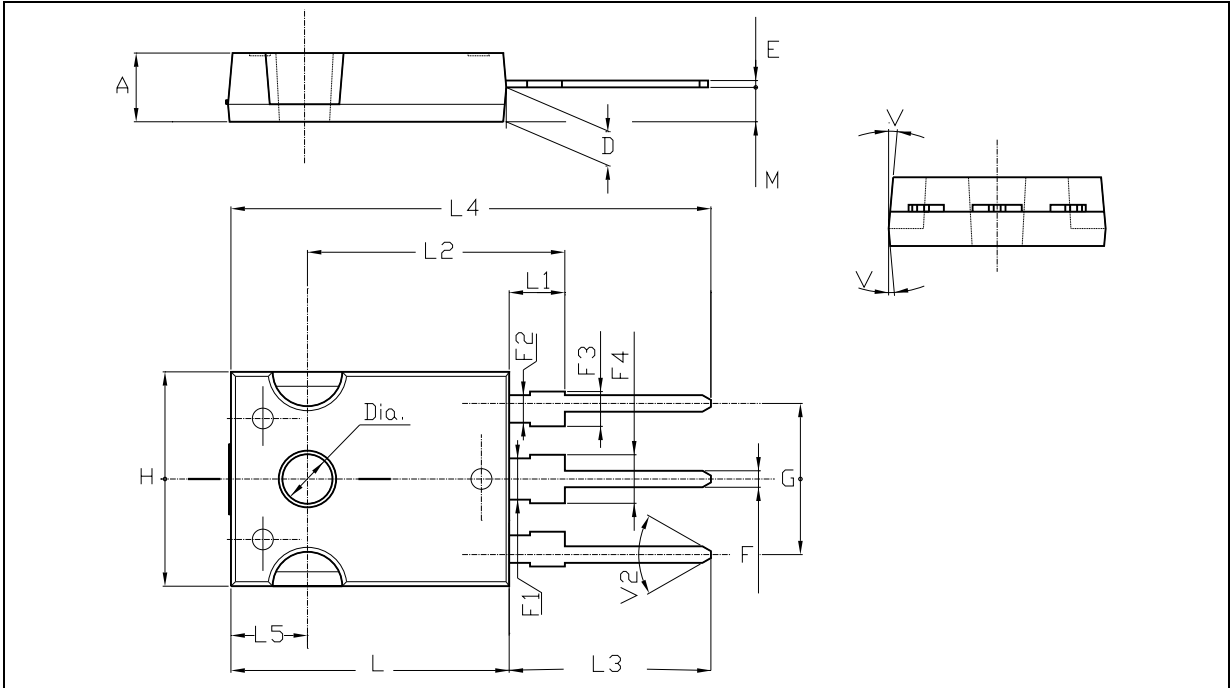


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



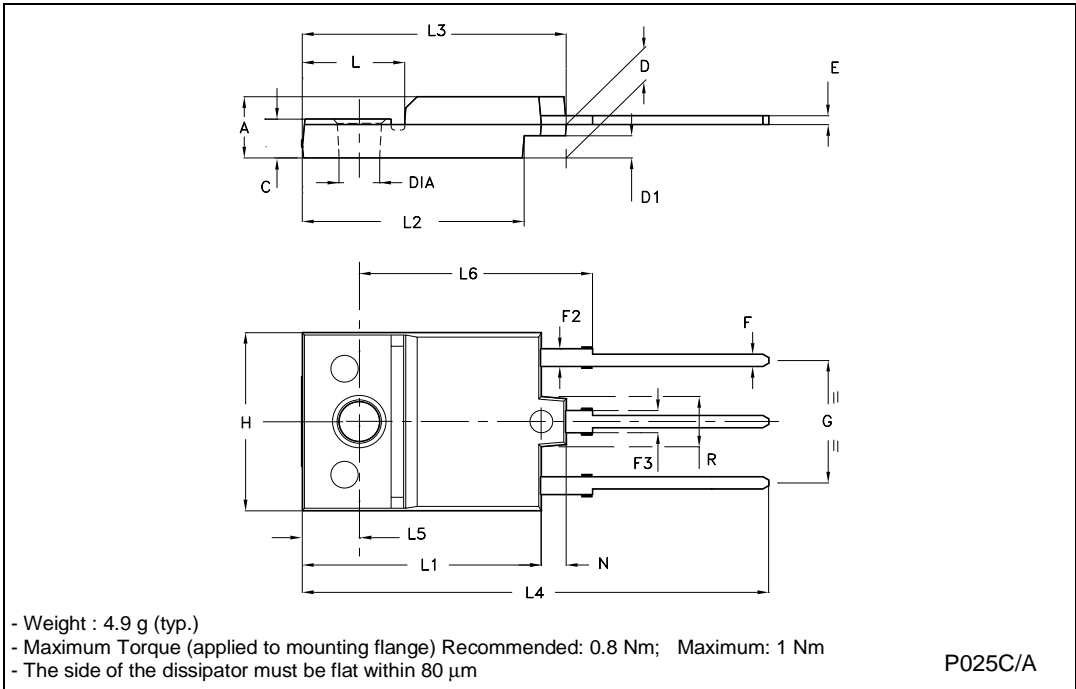
**TO-247 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
D	2.20		2.60	0.08		0.10
E	0.40		0.80	0.015		0.03
F	1		1.40	0.04		0.05
F1		3			0.11	
F2		2			0.07	
F3	2		2.40	0.07		0.09
F4	3		3.40	0.11		0.13
G		10.90			0.43	
H	15.45		15.75	0.60		0.62
L	19.85		20.15	0.78		0.79
L1	3.70		4.30	0.14		0.17
L2		18.50			0.72	
L3	14.20		14.80	0.56		0.58
L4		34.60			1.36	
L5		5.50			0.21	
M	2		3	0.07		0.11
V		5°			5°	
V2		60°			60°	
Dia	3.55		3.65	0.14		0.143



**ISOWATT218 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.211		0.222
C	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	1.05		1.25	0.041		0.049
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
G	10.80		11.20	0.425		0.441
H	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146





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